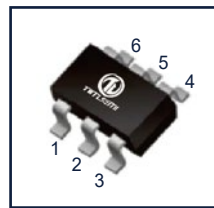
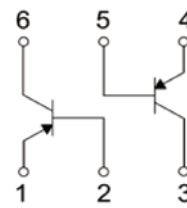


Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available(MMDT 5551)
- Ideal for Medium Power Amplification and Switching



SOT-363



Equivalent Circuit

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	0.2	W
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-160			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-10\mu\text{A}, I_C=0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB}=-120\text{V}, I_E=0$			-0.05	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3\text{V}, I_C=0$			-0.05	μA
$h_{FE(1)}$	DC current gain	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	50			
$h_{FE(2)}$		$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100		300	
$h_{FE(3)}$		$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50			
$V_{CE(sat)(1)}$	Collector-emitter saturation voltage	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.2	V
$V_{CE(sat)(2)}$		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
$V_{BE(1)}$	Base-emitter voltage	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-1	V
$V_{BE(2)}$		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1	V
f_T	Transition frequency	$V_{CE}=-10\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	100			MHz
C_{ob}	Output Capacitance	$V_{CB}=-10\text{V}, I_E=0\text{A}, f=1\text{MHz}$			6	pF
NF	Noise Figure	$V_{CE}=-5\text{V}, I_C=-200\mu\text{A}, R_S=10\Omega, f=1\text{kHz}$			8.0	dB

Ordering information

Product ID	Pack	Naming rule	Marking	$h_{FE(1)}$	Qty(PCS)
MMDT5401	SOT-363	MMDT5401 ↓ 产品名称 product name	K4M	100-300	3000



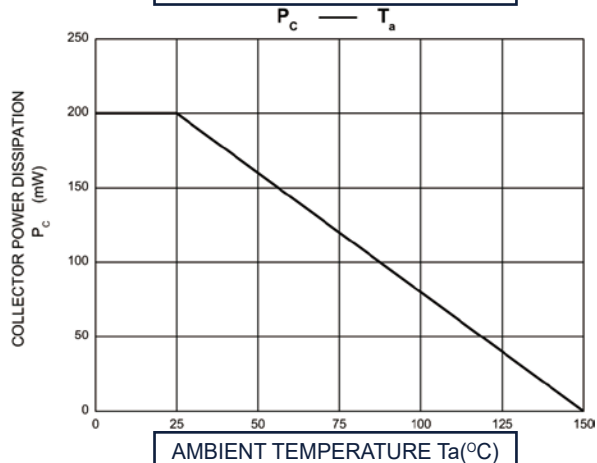
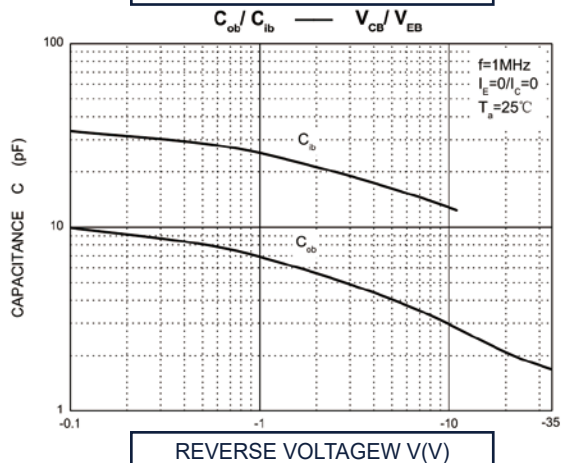
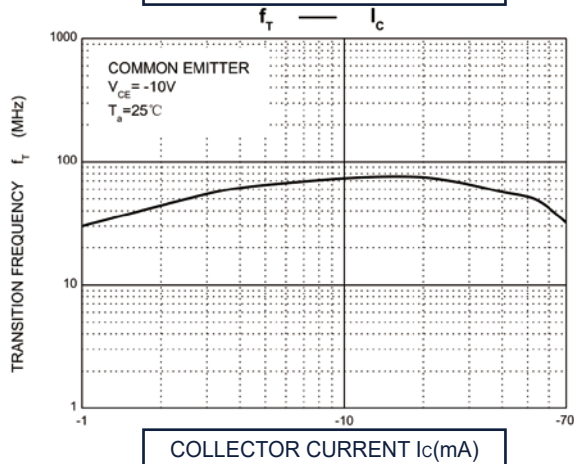
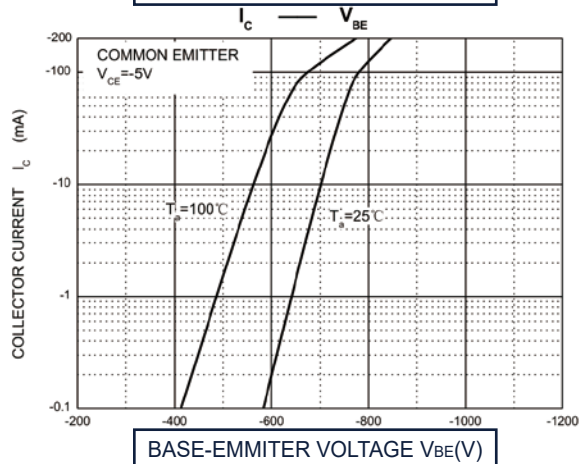
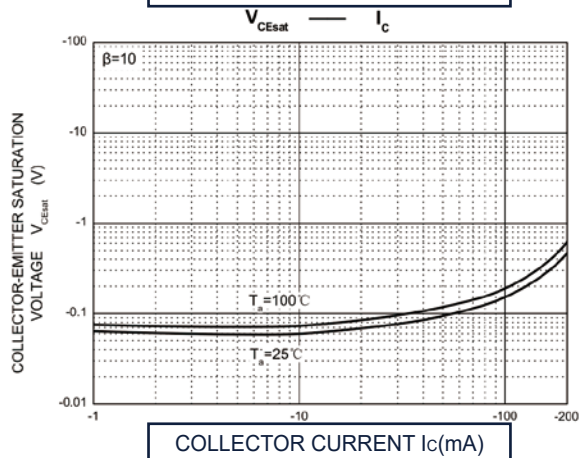
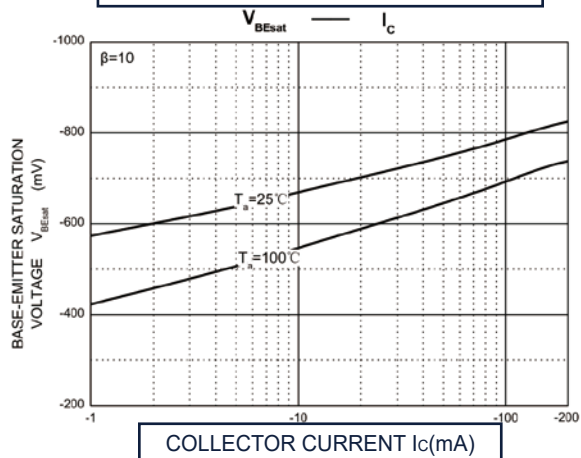
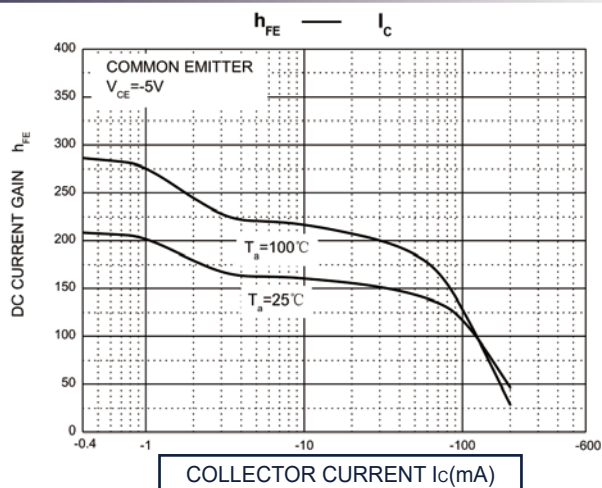
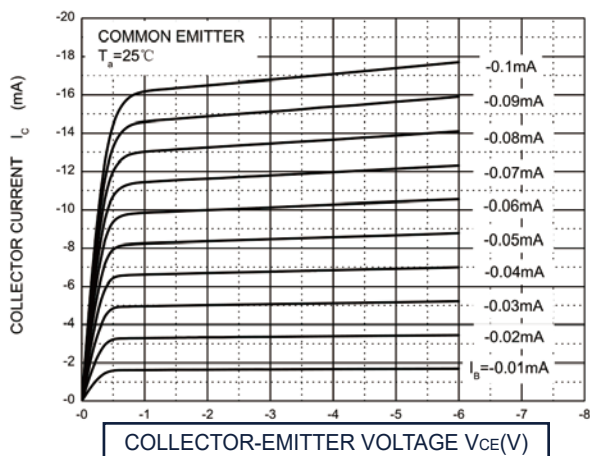
TWTLSEMI

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SOT-363 DUAL TRANSISTOR (PNP+PNP)

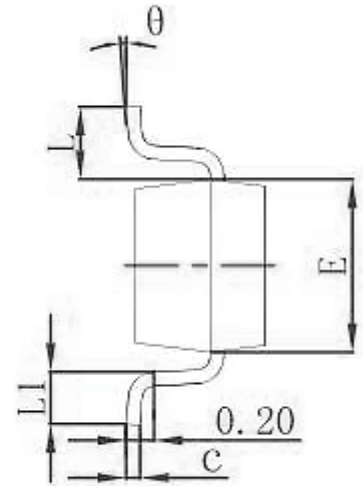
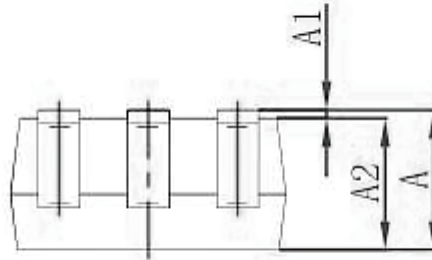
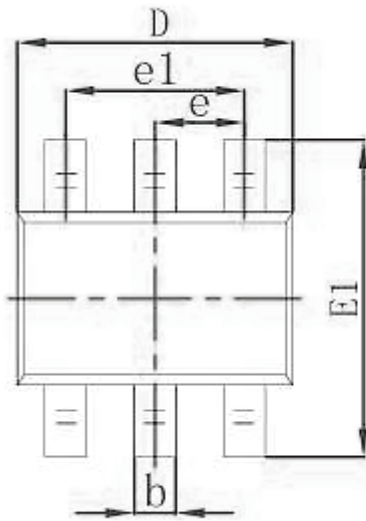
Typical Characteristics

Static Characteristic





SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°